TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC4075AP, TC74HC4075AF

TRIPLE 3-INPUT OR GATE

The TC74HC4075A is a high speed CMOS 3-INPUT OR GATE fabricated with silicon gate C²MOS technology.

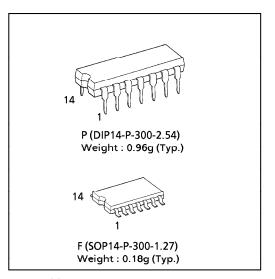
It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

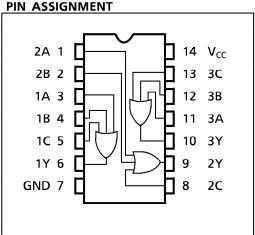
The internal circuit is composed of 4 stages including a buffered outputs, which provide high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

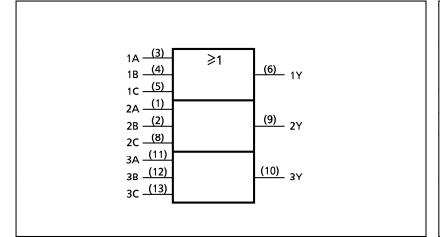
FEATURES:

- High Speed······t_{pd} = 8ns(typ.) at V_{CC} = 5V
- Low Power Dissipation ··········· $I_{CC} = 2\mu A(Max.)$ at $Ta = 25^{\circ}C$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\%$ V_{CC} (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... | I_{OH} | = I_{OL} = 4mA(Min.)
- Balanced Propagation Delays ····· t_{pLH} ≃ t_{pHL}
- Wide Operating Voltage Range ···· V_{CC} (opr.) = 2V ~ 6V
- Pin and Function Compatible with 4075B





IEC LOGIC SYMBOL



TRUTH TABLE

H X X H X H X H X X H H							
X X H H							
^ ^ '' ''							
L L L L							
X : Don't Care							

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TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	-0.5~7	V
DC Input Voltage	V _{IN}	−0.5~V _{CC} +0.5	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} + 0.5	٧
Input Diode Current	I _{IK}	± 20	mΑ
Output Diode Current	I _{ok}	±20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} / Ground Current	I _{cc}	± 50	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T _{stg}	−65~150	°C

*500mW in the range of Ta= -40° C~65°C. From Ta=65°C to 85 °C a derating factor of -10mW/°C shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	٧
Operating Temperature	T _{opr}	−40~85	°C
Input Rise and Fall Time	t _r , t _f	$0 \sim 1000 \text{ (V}_{CC} = 2.0\text{V)}$ $0 \sim 500 \text{ (V}_{CC} = 4.5\text{V)}$ $0 \sim 400 \text{ (V}_{CC} = 6.0\text{V)}$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL		. TEST CONDITION		V _{cc}	Ta = 25°C		Ta = −40~85°C		UNIT	
				(V)	MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}			2.0 4.5 6.0	1.50 3.15 4.20		_ _ _	1.50 3.15 4.20	_ _ _	V
Low - Level Input Voltage	VIL			2.0 4.5 6.0		 - -	0.50 1.35 1.80	_ _ _	0.50 1.35 1.80	V
High - Level Output Voltage	V _{OH}	V _{IN} =	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	_ _ _	1.9 4.4 5.9	_ _ _	v
	VIH OI VIL	V_{IH} or V_{IL}	$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	_	4.13 5.63	_	
Low - Level Output Voltage	V _{IN} =	$I_{OL} = 20 \mu A$	2.0 4.5 6.0	111	0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V	
	VIHO	V_{IH} or V_{IL}	$I_{OL} = 4$ mA $I_{OL} = 5.2$ mA	4.5 6.0	1 1	0.17 0.18	0.26 0.26	_	0.33 0.33	
Input Leakage Current	I _{I N}	$V_{IN} = V_{CC}$ or GND		6.0	-	1	±0.1	_	± 1.0	
Quiescent Supply Current	I _{CC}	$V_{IN} = V_{CC}$ or GND		6.0	_		1.0	_	10.0	μA

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, $Ta = 25^{\circ}C$, Input $t_r = t_f = 6ns$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t _{TLH} t _{THL}		_	4	8	
Propagation Delay Time	t _{pLH} t _{pHL}		_	8	15	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -40~85°		UNIT
FARAIVIETER		TEST CONDITION	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
	t _{TLH}		2.0	_	30	75	_	95	
Output Transition Time			4.5	_	8	15	-	19	
· '	t _{THL}		6.0	_	7	13	_	16	
	+		2.0	_	35	90	_	115	ns
Propagation Delay Time	t _{pLH}		4.5	_	11	18	_	23	
.,	t _{pHL}		6.0	_	9	15	_	20	
Input Capacitance	C _{IN}			_	5	10	_	10	n.E
Power Dissipation Capacitance	C _{PD} (1)			_	27	_	_	_	рF

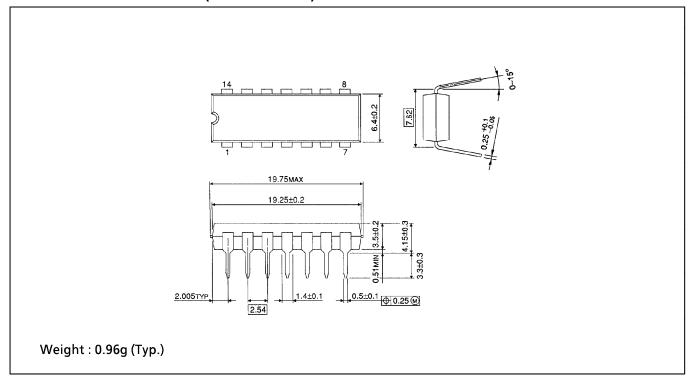
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3$ (per Gate)

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm

